



### 140V NPN DARLINGTON TRANSISTOR IN SOT223

### **Features**

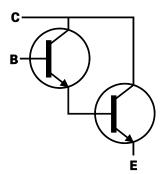
- BV<sub>CEO</sub> > 140V
- BVcso > 160V
- I<sub>C</sub> = 2A High Continuous Current
- NPN Darlington With Gain > 10k
- Guaranteed h<sub>FE</sub> Specified up to 1A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (FZT600BQ)

## **Mechanical Data**

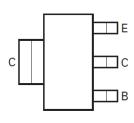
- Case: SOT223 (Type DN)
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)











Top View Pin-Out

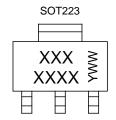
## Ordering Information (Note 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT600TA	AEC-Q101	FZT600	7	12	1000
FZT600BTA	AEC-Q101	FZT600B	7	12	1000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see http://www.diodes.com/products/packages.html.

## **Marking Information**



XXX XXXX = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 8= 2018) WW or  $\overline{W}W$  = Week Code (01~53)



# **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	160	V
Collector-Emitter Voltage	$V_{CEO}$	140	V
Emitter-Base Voltage	V <sub>EBO</sub>	10	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	I <sub>CM</sub>	4	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	P <sub>D</sub>	2.0	W	
Power Dissipation	(Note 7)		1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)		78.1		
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		R <sub>OJL</sub>	12.9		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	2000	V	2
Electrostatic Discharge—Machine Model	ESD MM	200	V	В

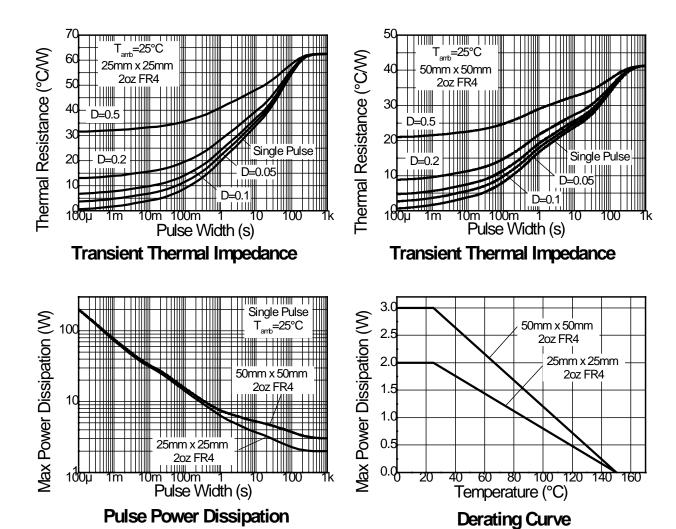
Notes:

- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

  6. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 6, except the device is mounted on 25mm  $\times$  25mm 1oz copper.
- 8. Same as Note 6, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

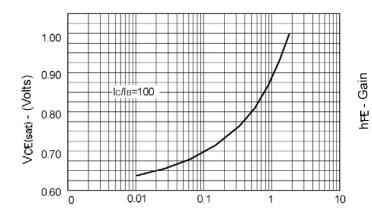
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	160	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BV <sub>CEO</sub>	140	_	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	10	_	_	V	$I_E = 100\mu A$
Collector-Base Cut-Off Current	I <sub>CBO</sub>	1	_	0.01 10	μΑ μΑ	V <sub>CB</sub> = 140V V <sub>CB</sub> = 140V, T <sub>A</sub> = +100°C
Collector-Emitter Cut-Off Current	ICES	-	_	10	μΑ	V <sub>CES</sub> = 140V
Emitter Cut-Off Current	I <sub>EBO</sub>	-	_	0.1	μA	V <sub>EB</sub> = 8V
Group A (FZT600)  DC Current Gain (Note 12)	h	1000 2000 1000	 	100,000 —	l	$I_{C} = 50mA, V_{CE} = 10V$ $I_{C} = 500mA, V_{CE} = 10V$ $I_{C} = 1A, V_{CE} = 10V$
Group B (FZT600B)	h <sub>FE</sub>	5000 10,000 5000	10,000 20,000 10,000	100,000 —		$I_C = 50mA, V_{CE} = 10V$ $I_C = 500mA, V_{CE} = 10V$ $I_C = 1A, V_{CE} = 10V$
Collector-Emitter Saturation Voltage (Note 12)	V <sub>CE(sat)</sub>		0.75 0.85	1.1 1.2	V	I <sub>C</sub> = 500mA, I <sub>B</sub> = 5mA I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA
Base-Emitter Saturation Voltage (Note 12)	V <sub>BE(sat)</sub>	_	1.7	1.9	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA
Base-Emitter Turn-On Voltage (Note 12)	V <sub>BE(on)</sub>	_	1.5	1.7	V	I <sub>C</sub> = 1A, V <sub>CE</sub> = 5V
Output Capacitance (Note 12)	C <sub>obo</sub>	_	10	15	pF	V <sub>CB</sub> = 10V, f = 1MHz
Current Gain-Bandwidth Product (Note 12)	f⊤	150	250	_	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA, f=20MHz
Turn-On Time	ton	_	0.75	_	μs	V <sub>CC</sub> = 10V, I <sub>C</sub> = 500mA
Turn-Off Time	t <sub>off</sub>		2.20		μs	$I_{B1} = -I_{B2} = 0.5 \text{mA}$

Note:

12. Measured under pulsed conditions. Pulse width ≤ 300 µs. Duty cycle ≤ 2%.

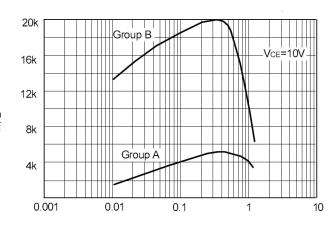


## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



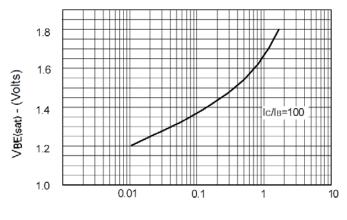


VCE(sat) v IC



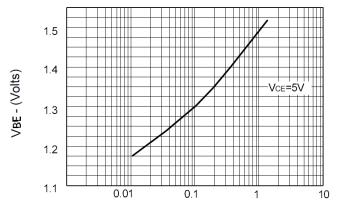
Ic - Collector Current (Amps)

hfe v IC



Ic - Collector Current (Amps)

VBE(sat) v IC



Ic - Collector Current (Amps)

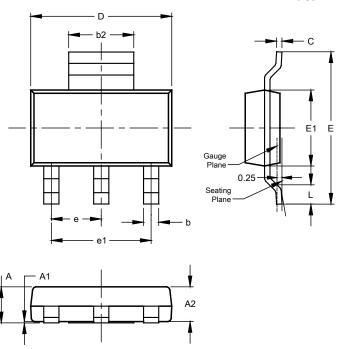
VBE(on) v IC



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT223 (Type DN)

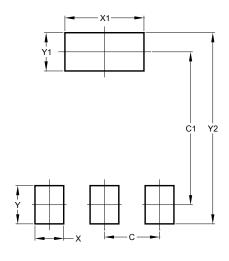


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α	_	1.70	_		
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70	_		
Е	6.70	7.30			
E1	3.30	3.70	_		
е	_	_	2.30		
e1		_	4.60		
L	0.85	_			
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: 13. For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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